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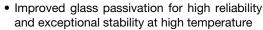
Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 16 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	16 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V <sub>TM</sub>	1.75 V			
I <sub>GT</sub>	60 mA			
T <sub>J</sub>	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

#### **FEATURES**





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- · Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		16	А			
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C			
I <sub>T(RMS)</sub>		35	A			
I <sub>TSM</sub>	50 Hz	340	Δ.			
	60 Hz	360	A A			
l <sup>2</sup> t	50 Hz	574	A2-			
	60 Hz	524	— A <sup>2</sup> s			
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V			
t <sub>q</sub>	Typical	110	μs			
T <sub>J</sub>		-65 to +125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} &= T_{J} & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-16RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \ ms$ 



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS		
Maximum average on-state current		100° oinuooi	180° sinusoidal conduction		16	Α	
at case temperature	I <sub>T(AV)</sub>	100 Siliusoi	idal conduction		85	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>				35	Α	
		t = 10 ms	No voltage		340		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		360	_	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	-	285	Α	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	300		
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage reapplied initial $T_J = T_J$ maximum	574			
	.0.	t = 8.3 ms			524	A <sup>2</sup> s	
	l <sup>2</sup> t	t = 10 ms	100 % V <sub>RRM</sub> reapplied		405		
		t = 8.3 ms			375		
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		5740	A²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		0.97	V		
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.24		
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < $I$ < $\pi$ x $I_{T(AV)}$ ), $I_J = I_J$ maximum		17.9	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.6	11122		
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 50 A, T <sub>J</sub> = 25 °C		1.75	V		
Maximum holding current	I <sub>H</sub>			and the same	130	A	
Latching current	ΙL	$I_{\rm J} = 25 {}^{\circ}{\rm C},  8$	T <sub>J</sub> = 25 °C, anode supply 6 V, resistive load		200	- mA	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \leq 600 \ V$			200	
Maximum rate of rise	$V_{DRM} \leq 800 \ V$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated\ V_{DRM}$ Gate pulse = 20 V, 15 $\Omega$ , $t_p = 6$ $\mu$ s, $t_r = 0.1$ $\mu$ s maximum $I_{TM} = (2\ x\ rated\ dI/dt)\ A$	180	A/μs
of turned-on current -	$V_{DRM} \leq 1000 \; V$	ui/ut		160	
	$V_{DRM} \leq 1600 \; V$			150	
Typical turn-on time		t <sub>gt</sub>	$T_J$ = 25 °C, at rated $V_{DRM}/V_{RRM}$ , $T_J$ = 125 °C	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \mu s$ , $dI/dt = -10 A/\mu s$	4	μs
Typical turn-off time		t <sub>q</sub>	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	

#### Note

•  $t_q$  = 10  $\mu s$  up to 600 V,  $t_q$  = 30  $\mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 100 % rated V <sub>DRM</sub>	100	V/µs
of off-state voltage	uv/ut	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	300 (1)	v/μS

#### Note

<sup>(1)</sup> Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 16RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$	$T_{.1} = T_{.1}$ maximum		8.0	w
Maximum average gate power	P <sub>G(AV)</sub>	ıj = ıj maximum		2.0	\ \v
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum		10	V
		T <sub>J</sub> = - 65 °C		90	mA
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	60	
		T <sub>J</sub> = 125 °C		35	
	V <sub>GT</sub>	T <sub>J</sub> = - 65 °C		3.0	
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C		2.0	V
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125		ç	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	R <sub>thJC</sub> DC operation		0.86		
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.35		K/W	
			TO NUT	TO DEVICE		
			20 (27.5)	25	lbf ⋅ in	
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m	
		( ton labilitation amount)	2.3 (3.1)	2.8	N · m	
Approximate weight			14		g	
Approximate weight			0.	49	OZ.	
Case style		See dimensions - link at the end of datasheet TO-48 (TO-208AA)		)		

△R <sub>thJC</sub> CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J$ maximum	K/W
60°	0.45	0.47		
30°	0.76	0.76		

#### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

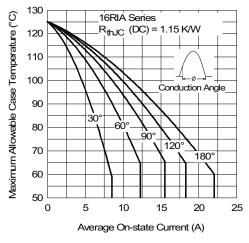


Fig. 1 - Current Ratings Characteristics

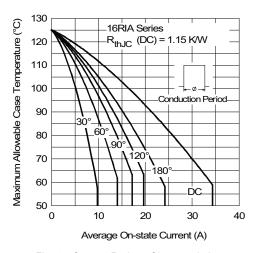


Fig. 2 - Current Ratings Characteristics

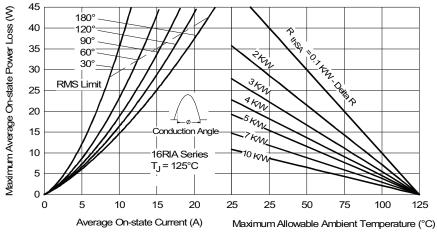


Fig. 3 - On-State Power Loss Characteristics

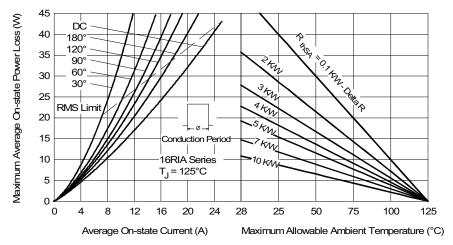


Fig. 4 - On-State Power Loss Characteristics

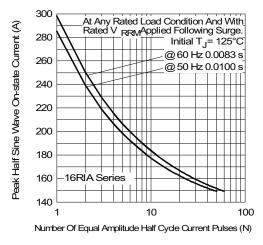


Fig. 5 - Maximum Non-Repetitive Surge Current

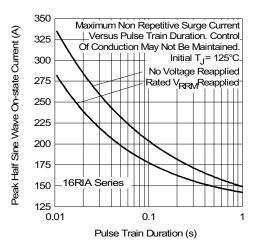


Fig. 6 - Maximum Non-Repetitive Surge Current

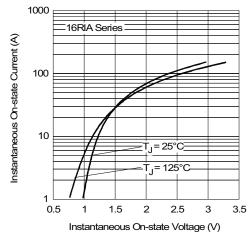


Fig. 7 - Forward Voltage Drop Characteristics

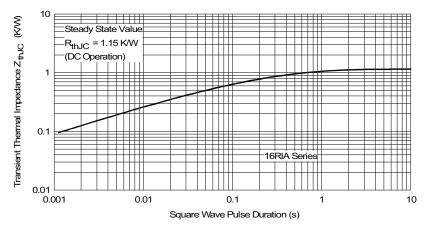


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

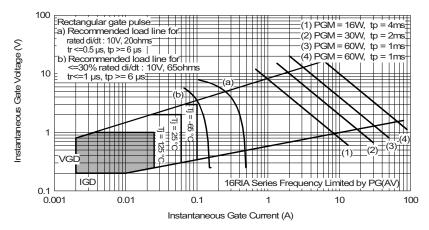
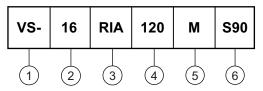


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)

None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

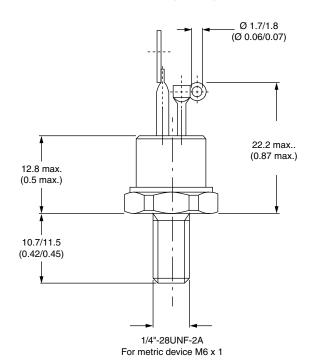
S90 = 1000 V/µs (special selection)

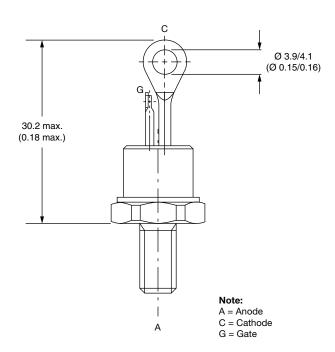
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

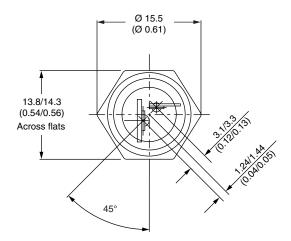


# TO-208AA (TO-48)

#### **DIMENSIONS** in millimeters (inches)









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